

ABSTRACT

RF semiconductor devices and methods of making the same are disclosed. In a disclosed method, a trench for defining an active region and an element isolation region is formed in a semiconductor substrate. One or more gate lines is then formed within the active region. Next, an insulating layer is formed on the semiconductor substrate and the gate lines. Contact holes are then formed in the insulating layer. Contact plugs are then formed in the contact holes. Thereafter, a conductive pattern is electrically connected with the contact plugs.